BAV74LT1

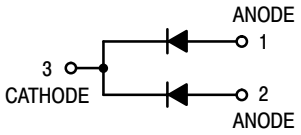
Monolithic Dual Switching Diode

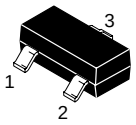
Features

- Pb−Free Package is Available

ON Semiconductor®

http://onsemi.com





SOT−23
CASE 318
STYLE 9

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	50	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

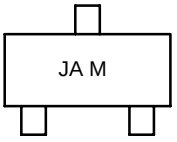
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1), T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in 99.5% alumina.

MARKING DIAGRAM



JA = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BAV74LT1	SOT−23	3000 / Tape & Reel
BAV74LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAV74LT3	SOT−23	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) **(EACH DIODE)**

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 5.0 μAdc)	$V_{(BR)}$	50	–	Vdc
Reverse Voltage Leakage Current, (Note 3) (V_R = 50 Vdc, T_J = 125°C) (V_R = 50 Vdc)	I_R	– –	100 0.1	μAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	2.0	pF
Forward Voltage (I_F = 100 mAdc)	V_F	–	1.0	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc, measured at I_R = 1.0 mA, R_L = 100 Ω)	t_{rr}	–	4.0	ns

3. For each individual diode while the second diode is unbiased.

Curves Applicable to Each Anode

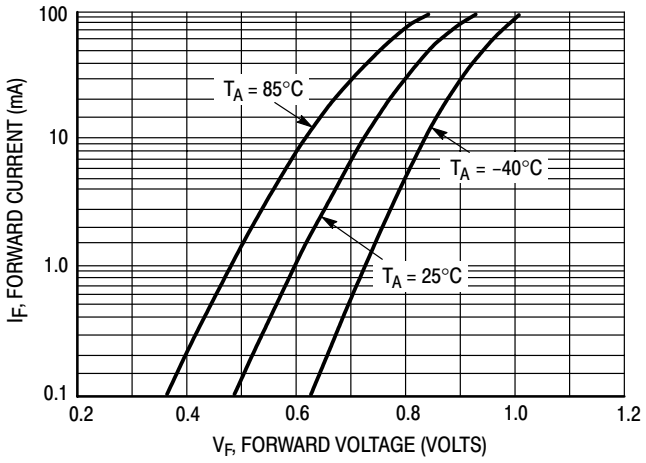


Figure 1. Forward Voltage

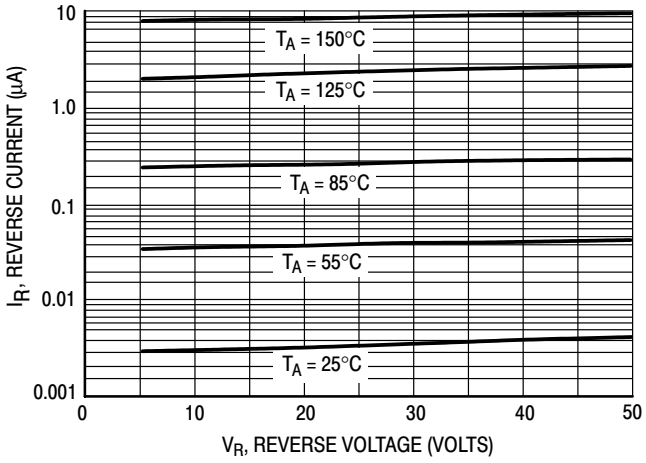


Figure 2. Leakage Current

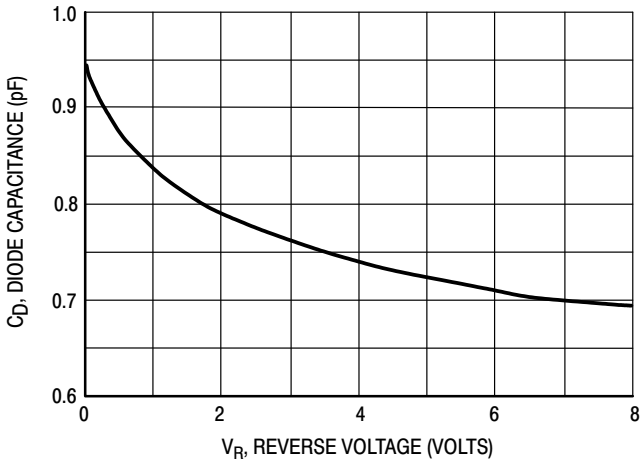
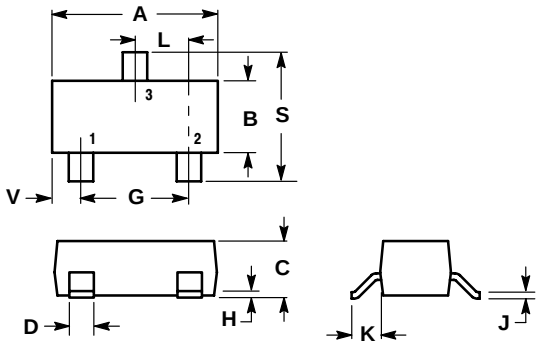


Figure 3. Capacitance

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AH

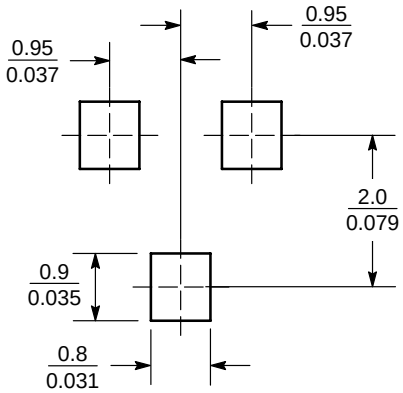


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−03 AND −07 OBSOLETE, NEW STANDARD 318−08.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

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For additional information, please contact your local Sales Representative.

BAV74LT1/D